

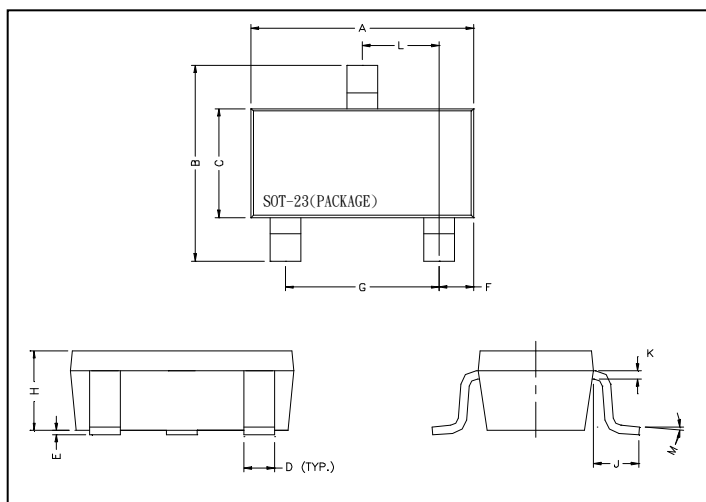
G706SD

**SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.03A**

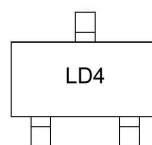
Description

The G706SD is designed for general purpose detection and high speed switching.

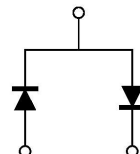
Package Dimensions



Marking:



Circuit :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

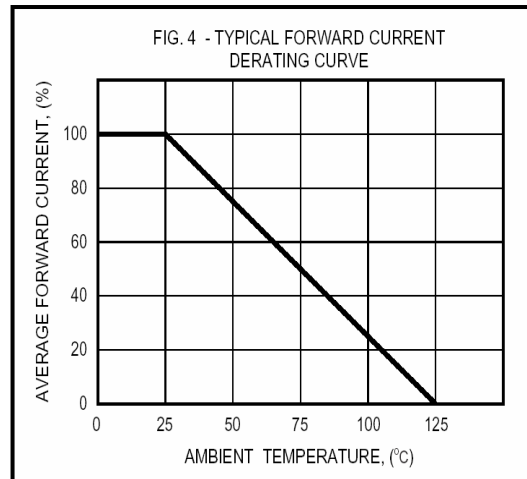
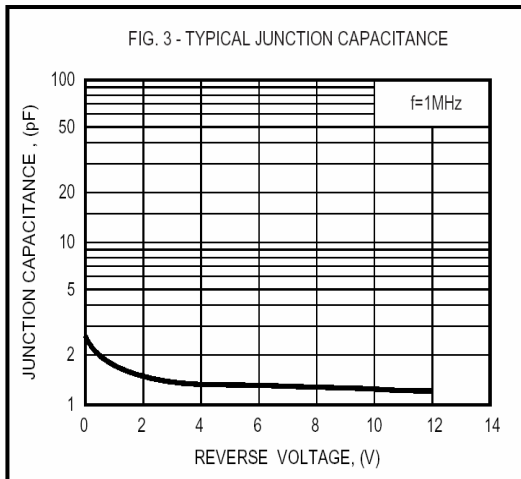
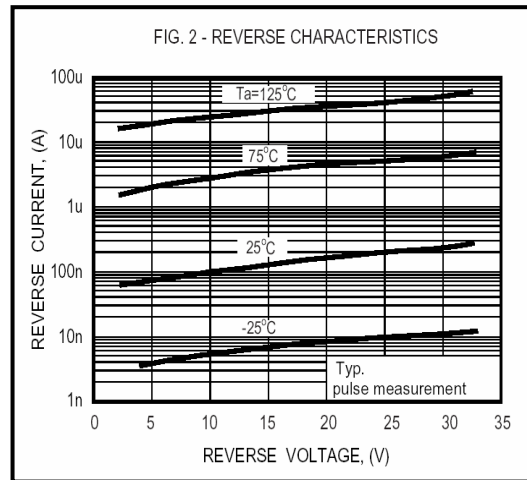
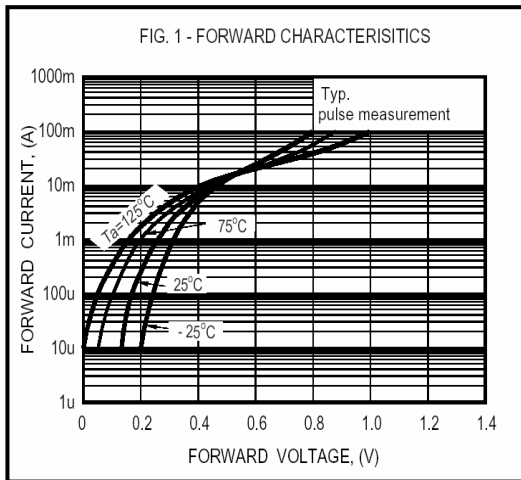
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	45	V
Maximum RMS Voltage	V _{RMS}	32	V
Maximum DC Blocking Voltage	V _{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	0.2	A
Typical Junction Capacitance between Terminal	C _J	2.0	pF
Maximum Average Forward Rectified Current	I _o	0.03	A
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Characteristics	Symbol	Typ.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _F	0.37	V	I _F = 1mA
Maximum Average Reverse Current	I _R	1.0	uA	V _R = 10V

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165